



SUNDAY 26 MAY

15:30

Registration of Participants

17:30-19:30

Welcome Reception



View full Program online



MONDAY 27 MAY	
08:15	Admissions
08:45	Opening Notes <i>MoM1: Bulk Growth</i>
Ch: Kuramata (NCT), Mu (Shandong U), Taishi (Shinshu U), Igarashi (NCT) Hangzhou Fujia	
10:15	Refreshments
10:45	<i>MoM2 Vapor Phase Epitaxy</i>
Ch: Popp* (IKZ), Chou (IKZ), Osinski (Agnitron) Kumagai (TUAT), LayTec	
12:30	Lunch break
14:15	<i>MoA1 kappa-Ga₂O₃, Ga₂O₃/III-N, MBE</i>
Ch: Fornari (Parma U), Monroy (U Grenoble), McCandless (Cornell U), Raghuvansy (U Bremen), Sacchi (U Parma), Karg (U Bremen)	
15:40	Refreshments
16:25	<i>MoA2 MBE, Polymorphism</i>
Ch: Schlom (Cornell U), Bertoni (U Milano), Galeckas (U Oslo), Janzen (TU Berlin)	
17:35-19:35	<i>MoP 1-41: Monday Poster Session</i>
Bulk β -Ga ₂ O ₃ , Polymorphs and κ -Ga ₂ O ₃ , Growth mechanisms, & Ga ₂ O ₃ /III-N	

TUESDAY 28 MAY	
08:15	Admissions
08:45	<i>TuM1: Doping & Vacancies 1</i>
Ch: Van de Walle* (UCSB) Zhelezova (U Helsinki) Noseges (AFRL)	
10:10	Refreshments
10:40	<i>TuM2 Doping & Vacancies 2</i>
Ch: Seyidov (IKZ), Hommedal (U Oslo), Moorthy Babu (Anna U), Wen (U Madison), Yoshinaga (TUAT)	
12:30	Lunch break
14:15	<i>TuA1 Defects and γ-Ga₂O₃ 1</i>
Ch: Gann (Cornell U), Demchenko (IPP Warsaw), Kuznetsov (U Oslo), Hwang (OSU), Lee (U Michigan), Martin (U Aachen)	
15:50	Refreshments
16:20	<i>TuA1 Defects and γ-Ga₂O₃ 2</i>
Ch: Ratcliff (U Bristol), Wouters (IKZ), Pieczulewski (Cornell U), Frodason (U Oslo)	
17:30-19:30	<i>TuP 1-44: Tuesday Poster Session</i>
Doping, γ -Ga ₂ O ₃ , Characterization, Detectors, & Thermal properties	

WEDNESDAY 29 MAY	
08:15	Admissions
08:45	<i>WeM1 β-Ga₂O₃ alloys</i>
Ch: Mazzolini (U Parma), Koreishi (TIT), Togashi (Sophia U), Rehm (IKZ), Seyidov (IKZ)	
10:25	Refreshments
11:00	<i>WeM2 From α-Ga₂O₃ to α-Al₂O₃</i>
Ch: Jinno (U Tokyo), Maruzane (U Strathclyde), Dang (U Canterbury), Vogt (U Leipzig), Schubert (U Lincoln-N.), Okumura (U	
12:30	Lunch break & WeP 1-53: Wednesday Poster Session
(Al,Ga) ₂ O ₃ , Alloys, α -phase, Diodes, NiO/Ga ₂ O ₃ , MOSFETs	
14:30	Excursions
17:30-20:00	Banquet

THURSDAY 30 MAY	
08:15	Admissions
08:45	<i>ThM1 Power Devices & Diodes</i>
Ch: Higashiwaki* (Osaka MU), Hendricks (AFRL) Farzana (Iowa SU)	
10:10	Refreshments
10:40	<i>ThM2 Diodes and High Voltage</i>
Ch: Xu (USTC), Dang (U Canterbury), Cromer (U Stanford), Masten (NRL), Smith (Cornell U), Arima (TDK)	
12:10	Lunch break
14:00	<i>ThA1 NiO/Ga₂O₃ heterojunctions for Diodes</i>
Ch: Ye (Nanjing U), Xu (USTC), Gilankar (Arizona SU), Xu (USTC), Tadjer (NRL)	
15:25	Refreshments
16:00	<i>ThA2 MOSFETs & NiO/Ga₂O₃ heterojunctions</i>
Ch: Zhou (USTC), Oshima (NIMS), Tetzner (FBH), Dryden (Cornell U), Wang (NICT), Liddy (AFRL)	
17:40-19:15	<i>Rump Session: Industry Perspective on Ga₂O₃</i>

FRIDAY 31 MAY	
08:15	Admissions
08:45	<i>FrM1 Advanced Device Characterization / Thermal Properties</i>
Ch: McCluskey (Washington SU), Fregolent (U Padova), Yao (JFCC), Lundh (NRL), Liao (NRL), Wagner (PDI), Nandi (U Bristol)	
10:40	Refreshments
11:10	<i>FrM2 Detectors</i>
Ch: Shimazoe (Kyoto IT) Zhao (USTC), Zhao (USTC) Hou (USTC), Zhang (Xiangtan U)	
12:25	Lunch break
14:15	<i>FrA1 Rutile GeO₂ as novel ultrawide bandgap semiconductor</i>
Ch: Kioupakis (U Michigan), Wang (U Michigan), Galazka (IKZ), Chen (PDI), Tornatzky (PDI)	
16:10	Refreshments
16:30	<i>FrA2 Late News</i>
Ch: Singisetti (U Buffalo), Myamoto (NCT), Li (KAUST)	
17:25	Award Ceremony
17:40-17:55	Closing

Bold*: Keynote Speaker
Bold: Invited Speaker